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Kind regards,

Team Nexperia

74LVC1GU04-Q100

Unbuffered inverter

Rev. 2 — 13 December 2016

Product data sheet

1. General description

The 74LVC1GU04-Q100 is a single unbuffered inverter.

The input can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pf}$, $R = 0\text{ }\Omega$)
- $\pm 24\text{ mA}$ output drive ($V_{CC} = 3.0\text{ V}$)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Input accepts voltages up to 5 V

3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74LVC1GU04GW-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74LVC1GU04GV-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SC-74A	plastic surface-mounted package; 5 leads	SOT753



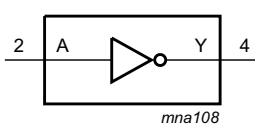
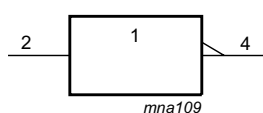
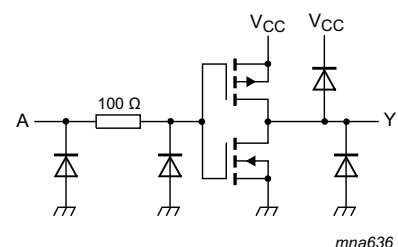
4. Marking

Table 2. Marking codes

Type number	Marking ^[1]
74LVC1GU04GW-Q100	VD
74LVC1GU04GV-Q100	VU4

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

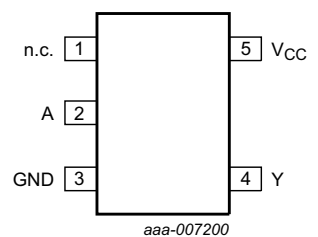
5. Functional diagram

 <p><i>mna108</i></p>	 <p><i>mna109</i></p>	 <p><i>mna636</i></p>
Fig 1. Logic symbol	Fig 2. IEC logic symbol	Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

74LVC1GU04-Q100



aaa-007200

Fig 4. Pin configuration SOT353-1 and SOT753

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
n.c.	1	not connected
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V _{CC}	5	supply voltage

7. Functional description

Table 4. Function table^[1]

Input (A)	Output (Y)
L	H
H	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I_{IK}	input clamping current	$V_I < 0$ V	-	-50	mA
V_I	input voltage		-0.5	+6.5	V
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	±50	mA
V_O	output voltage	Active mode	-0.5	$V_{CC} + 0.5$	V
I_O	output current	$V_O = 0$ V to V_{CC}	-	±50	mA
I_{CC}	supply current		-	+100	mA
I_{GND}	ground current		-	-100	mA
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to $+125$ °C	-	250	mW
T_{stg}	storage temperature		-65	+150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When $V_{CC} = 0$ V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage	Active mode	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.65$ V to 2.7 V	0	-	20	ns/V
		$V_{CC} = 2.7$ V to 5.5 V	0	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ ^[1]	Max	Unit
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 5.5 V	0.75 × V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 5.5 V	-	-	0.25 × V _{CC}	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -100 μA; V _{CC} = 1.65 V to 5.5 V	V _{CC} - 0.1	-	-	V
		I _O = -4 mA; V _{CC} = 1.65 V	1.2	-	-	V
		I _O = -8 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	2.2	-	-	V
		I _O = -24 mA; V _{CC} = 3.0 V	2.3	-	-	V
		I _O = -32 mA; V _{CC} = 4.5 V	3.8	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 μA; V _{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.3	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.4	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.55	V
		I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	±0.1	±1	μA
I _{CC}	supply current	V _I = 5.5 V or GND; I _O = 0 A; V _{CC} = 1.65 V to 5.5 V	-	0.1	4	μA
C _I	input capacitance	V _{CC} = 3.3 V; V _I = GND to V _{CC}	-	6	-	pF
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 5.5 V	0.8 × V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 5.5 V	-	-	0.2 × V _{CC}	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -100 μA; V _{CC} = 1.65 V to 5.5 V	V _{CC} - 0.1	-	-	V
		I _O = -4 mA; V _{CC} = 1.65 V	0.95	-	-	V
		I _O = -8 mA; V _{CC} = 2.3 V	1.7	-	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	1.9	-	-	V
		I _O = -24 mA; V _{CC} = 3.0 V	2.0	-	-	V
		I _O = -32 mA; V _{CC} = 4.5 V	3.4	-	-	V

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ ^[1]	Max	Unit
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 μA; V _{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.7	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.6	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.80	V
		I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.80	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	±0.1	±1	μA
I _{CC}	supply current	V _I = 5.5 V or GND; I _O = 0 A; V _{CC} = 1.65 V to 5.5 V	-	-	4	μA

[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit, see [Figure 8](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	A to Y; see Figure 5 ^[2]						
		V _{CC} = 1.65 V to 1.95 V	0.3	1.7	5.0	0.3	6.5	ns
		V _{CC} = 2.3 V to 2.7 V	0.3	1.3	4.0	0.3	5.5	ns
		V _{CC} = 2.7 V	0.5	1.7	5.0	0.5	6.5	ns
		V _{CC} = 3.0 V to 3.6 V	0.5	1.6	3.7	0.5	5.0	ns
		V _{CC} = 4.5 V to 5.5 V	0.5	1.3	3.0	0.5	4.0	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} ; V _{CC} = 3.3 V ^[3]	-	14.9	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

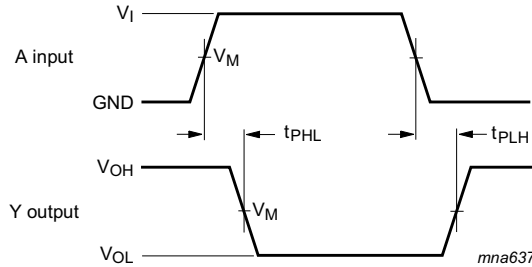
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

∑(C_L × V_{CC}² × f_o) = sum of outputs.

12. Waveforms

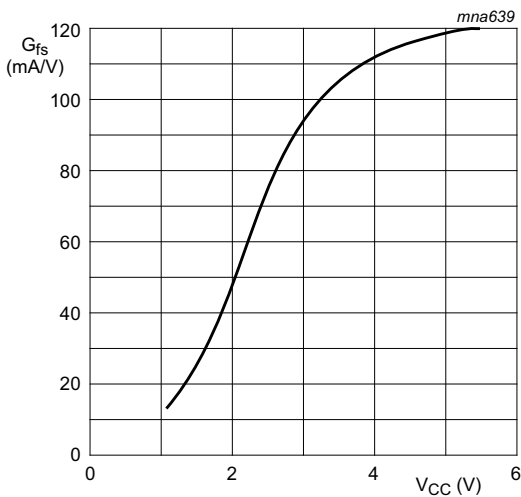


Measurement points are given in [Table 9](#).
 VOL and VOH are typical output voltage levels that occur with the output load.

Fig 5. The input A to output Y propagation delay times

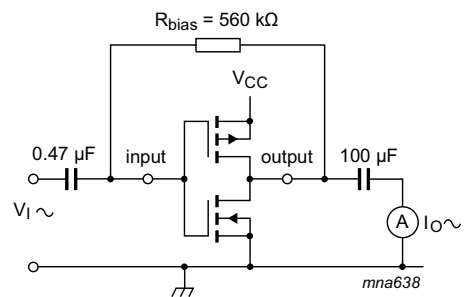
Table 9. Measurement points

Supply voltage	Input	Output
VCC	VM	VM
1.65 V to 1.95 V	0.5 × VCC	0.5 × VCC
2.3 V to 2.7 V	0.5 × VCC	0.5 × VCC
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	0.5 × VCC	0.5 × VCC



Tamb = 25 °C.

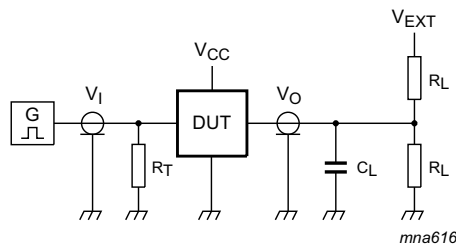
Fig 6. Typical forward transconductance as a function of supply voltage



$$G_{fs} = \frac{\Delta I_o}{\Delta V_I}$$

f_i = 1 kHz at V_O is constant

Fig 7. Test set-up for measuring forward transconductance



Test data is given in [Table 10](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 8. Test circuit for measuring switching times

Table 10. Test data

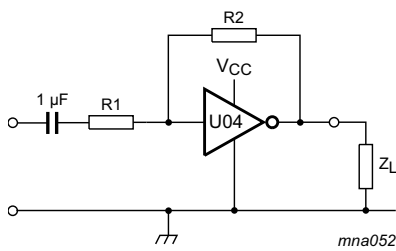
Supply voltage	Input		Load		V_{EXT}
V_{CC}	V_I	$t_r = t_f$	C_L	R_L	t_{PLH}, t_{PHL}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 k Ω	open
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open

13. Application information

Some applications are:

- Linear amplifier (see [Figure 9](#))
- In crystal oscillator design (see [Figure 10](#))

Remark: All values given are typical unless otherwise specified.



$$V_{o(p-p)} = V_{CC} - 1.5 \text{ V centered at } 0.5V_{CC}.$$

$$A_u = - \frac{G_{OL}}{1 + \frac{R1}{R2}(1 + G_{OL})}$$

G_{OL} = loop gain.

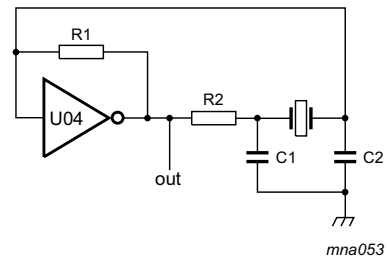
A_u = voltage amplification.

$R1 \geq 3 \text{ k}\Omega$, $R2 \leq 1 \text{ M}\Omega$

$Z_L > 10 \text{ k}\Omega$; $A_{OL} = 20$ (typ.)

Typical unity gain bandwidth product is 5 MHz.

Fig 9. Used as a linear amplifier



$C1 = 47 \text{ pF}$ (typ.)

$C2 = 22 \text{ pF}$ (typ.)

$R1 = 1 \text{ M}\Omega$ to $10 \text{ M}\Omega$ (typ.)

$R2$ optimum value depends on the frequency and required stability against changes in V_{CC} or average minimum I_{CC} (I_{CC} is typically 2 mA at $V_{CC} = 3.3 \text{ V}$ and $f = 10 \text{ MHz}$).

Fig 10. Crystal oscillator configuration

14. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

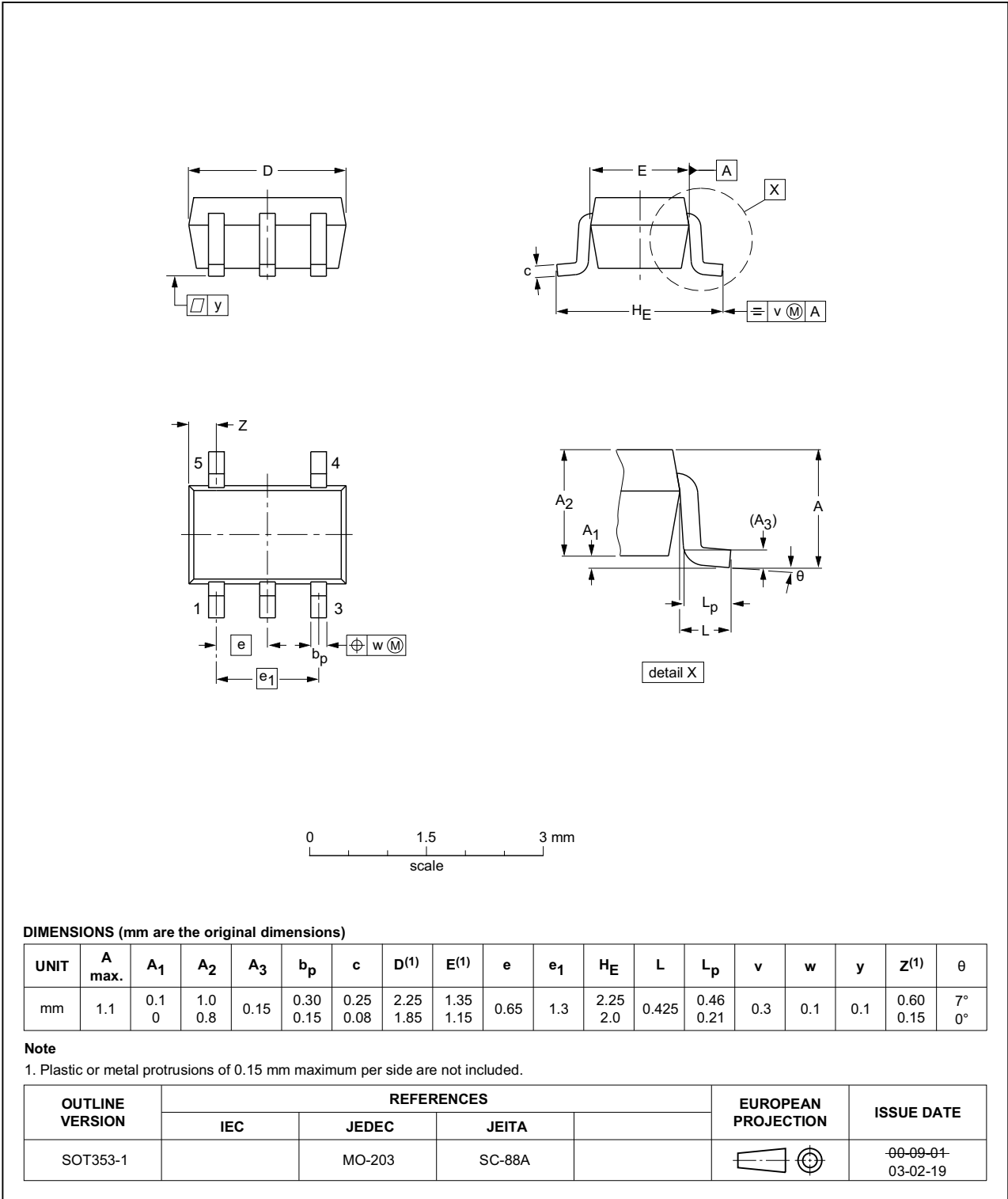


Fig 11. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

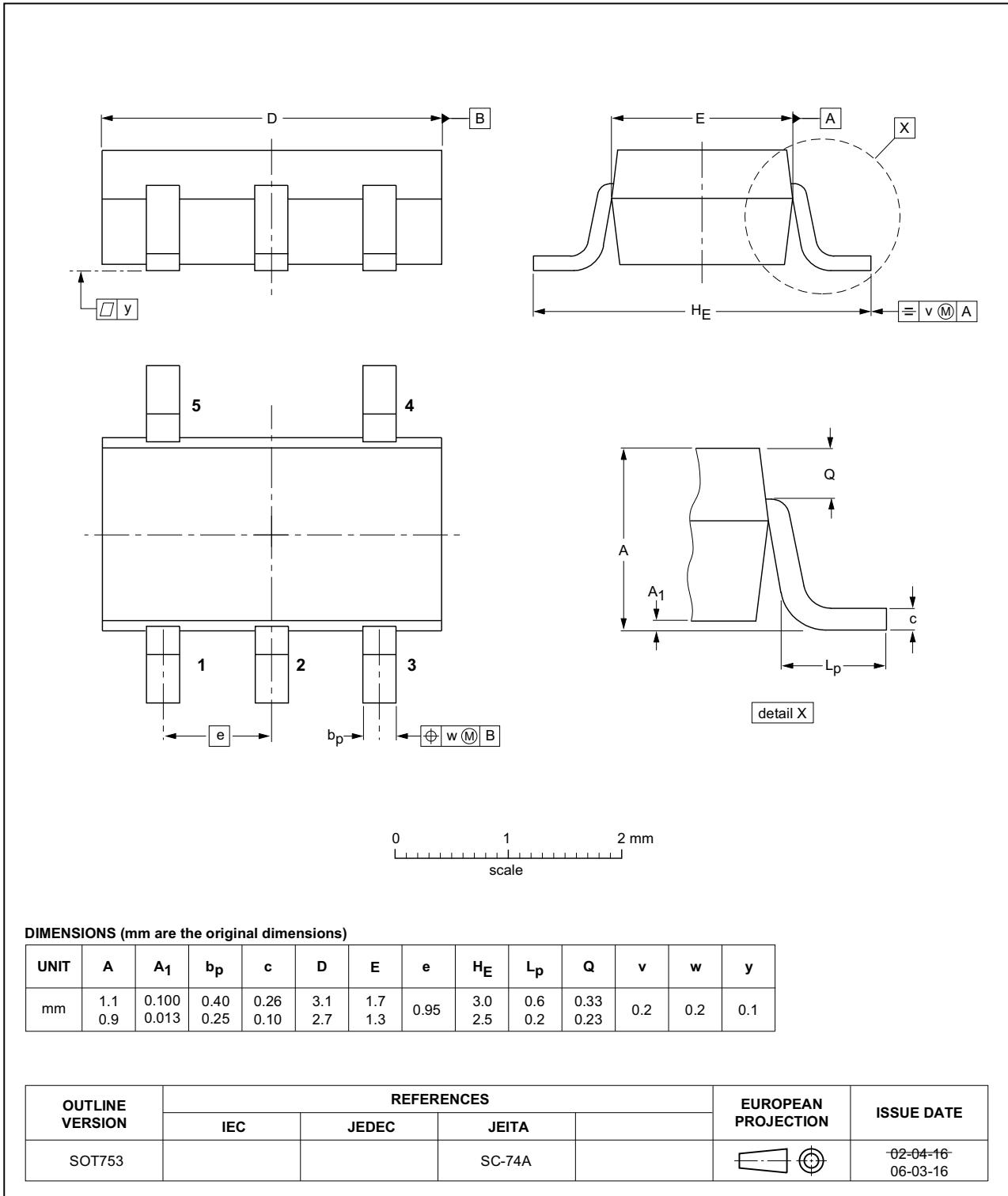


Fig 12. Package outline SOT753 (SC-74A)

15. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model

16. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1GU04_Q100 v.2	20161213	Product data sheet	-	74LVC1GU04_Q100 v.1
Modifications:	• Table 7 : The maximum limits for leakage current and supply current have changed.			
74LVC1GU04_Q100 v.1	20130514	Product data sheet	-	-

17. Legal information

17.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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